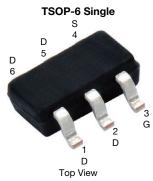
SQ3418AEEV

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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



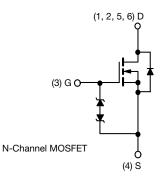
Marking Code: 8M

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.032			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.042			
I _D (A)	8			
Configuration	Single			

FEATURES

- TrenchFET[®] power MOSFET
- Typical ESD protection 800 V
- AEC-Q101 qualified d
- 100 % $\rm R_g$ and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3418AEEV (for detailed order number please see www.vishav.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unless	s otherwise noted	ł)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40	V	
Gate-source voltage		V _{GS}	± 20		
Continuous drain current	$T_C = 25 \ ^{\circ}C \ ^{a}$	I_	8		
	T _C = 125 °C	D ID	5		
Continuous source current (diode conduction)		I _S	4	А	
Pulsed drain current ^b		I _{DM}	32		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	11		
Single pulse avalanche energy		E _{AS}	6	mJ	
Maximum power dissipation ^b	T _C = 25 °C	PD	5	W	
	T _C = 125 °C	гD	1.6	vv	
Operating junction and storage temperature rar	nge	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^c	R _{thJA}	110	°C/W	
Junction-to-foot (drain)		R _{thJF}	30	C/ W	

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

d. Parametric verification ongoing

S21-1074-Rev. B, 15-Nov-2021

1



SQ3418AEEV

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•					<u> </u>		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	V	
Gate-source leakage		$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	-	± 2	μA	
	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 1	mA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
		$V_{GS} = 10 V$	I _D = 5 A	-	0.026	0.032	Ω	
Drain acuras en stata registance à	Б	V _{GS} = 10 V	I _D = 5 A, T _J = 125 °C	-	-	0.050		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5 A, T _J = 175 °C	-	-	0.061		
		$V_{GS} = 4.5 V$	I _D = 4 A	-	0.032	0.042		
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 4 A	-	13	-	S	
Dynamic ^b					•			
Input capacitance	C _{iss}		V _{DS} = 20 V, f = 1 MHz	-	450	675	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	80	120		
Reverse transfer capacitance	C _{rss}			-	41	62		
Total gate charge ^c	Qg		V _{DS} = 20 V, I _D = 4 A	-	8.2	12.4	nC	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V		-	1.3	-		
Gate-drain charge ^c	Q _{gd}	_		-	1.9	-		
Gate resistance	Rg	f = 1 MHz		0.9	1.8	2.7	Ω	
Turn-on delay time ^c	t _{d(on)}			-	6	9		
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 4 \Omega$ $\text{I}_{D} \cong 5 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	28	38	- ns	
Turn-off delay time ^c	t _{d(off)}			-	12	16		
Fall time ^c	t _f			-	37	49		
Source-Drain Diode Ratings and Cha	racteristics T _C = 2	25 °C ^b						
Pulsed current ^a	I _{SM}			-	-	32	А	
Forward voltage	V _{SD}	I _F = 3 A, V _{GS} = 0		-	0.8	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

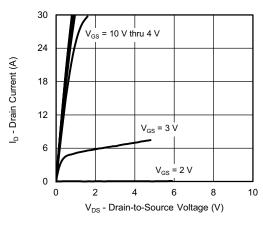
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

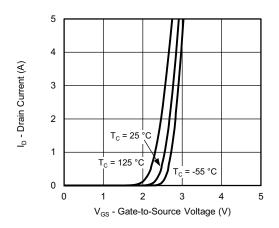
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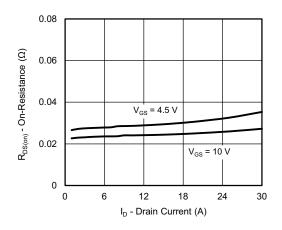
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



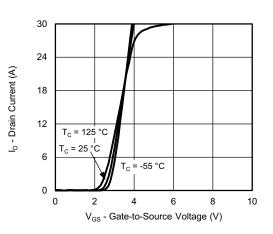
Output Characteristics



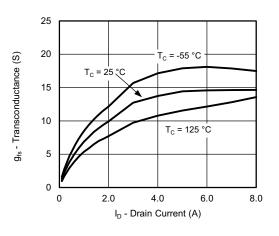
Transfer Characteristics



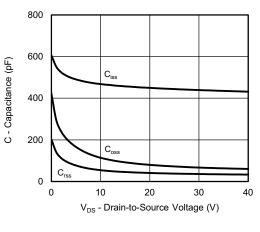
On-Resistance vs. Drain Current



Transfer Characteristics







Capacitance

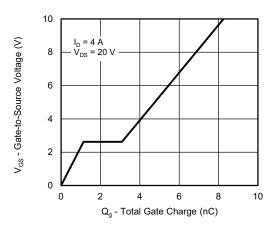
S21-1074-Rev. B, 15-Nov-2021

3

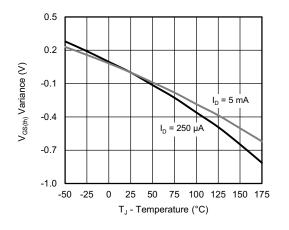
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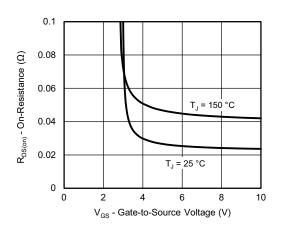
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



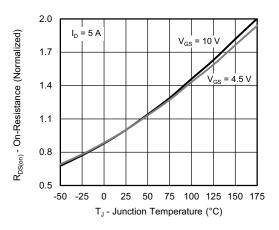
Gate Charge



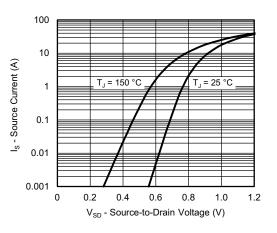
Threshold Voltage



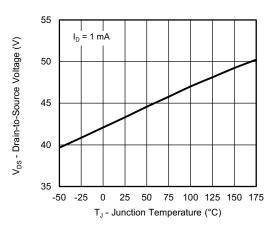
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



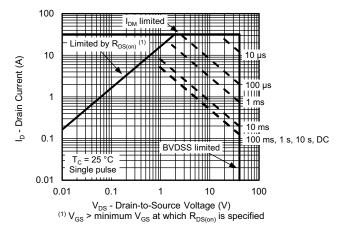
Drain Source Breakdown vs. Junction Temperature

S21-1074-Rev. B, 15-Nov-2021

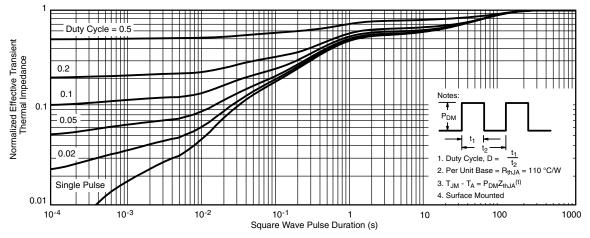
4



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



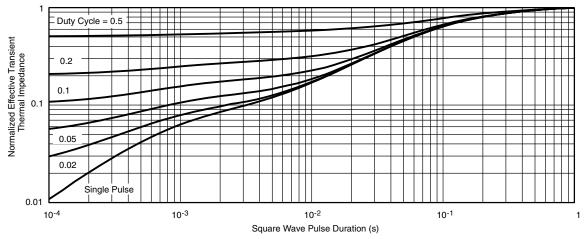




Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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